

05/31/01
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PATENT APPLICATION
TRANSMITTAL

Only for new nonprovisional applications under 37 CFR 1.53(b)

Attorney Docket No. 209291US0

First Inventor or Application Identifier Hiroyuki NAGASAWA, et al.

Title METHOD OF MANUFACTURING SILICON CARBIDE, SILICON CARBIDE, COMPOSITE MATERIAL, AND SEMICONDUCTOR ELEMENT

Assignee Name HOYA CORPORATION

Assignee Address 7-5, Naka-Ochiai 2-chome, Shinjuku-ku, Tokyo 161-0032, Japan

APPLICATION ELEMENTS

See MPEP chapter 600 concerning utility patent application contents

1. Fee Transmittal Form (e.g. PTO/SB/17)
(Submit an original and a duplicate for fee processing)

2. Specification Total Sheets **36**

3. Drawing(s) (35 U.S.C. 113) Total Sheets **7** (Formal)

4. Oath or Declaration Total Pages
 a. Newly executed (original or copy)
 b. Copy from a prior application (37 C.F.R. §1.63(d))
(for continuation / divisional w/ box 17 completed)
 i. DELETION OF INVENTOR(S)
Signed statement attached deleting inventor(s) named in
the prior application, see 37 C.F.R. §1.63(d)(2) and
1.33(b).

5. CD-ROM or CD-R in duplicate, large table or Computer
Program (Appendix)

6. Nucleotide and/or Amino Acid Sequence Submission
(if applicable, all necessary)
 a. Computer Readable Form (CRF)
 b. Specification or Sequence Listing on:
 i. CD-ROM or CD-R (2 copies); or
 ii. Paper
 c. Statements verifying identity of above copies

17. If a CONTINUING APPLICATION, check appropriate box and supply the requisite information below:

 Continuation Divisional Continuation-in-part (CIP) of prior application no.

Prior application information: Examiner: Group Art Unit

For CONTINUATION OR DIVISIONAL APPS only: The entire disclosure of the prior application, from which an oath or declaration is supplied under Box 4b, is considered a part of the accompanying continuation or divisional application and is hereby incorporated by reference. The incorporation can only be relied upon when a portion has been inadvertently omitted from the submitted application parts.

18. Amend the specification by inserting before the first line the sentence:

This application is a Continuation Division Continuation-in-part (CIP)
of application Serial No. Filed on

Which was published in English

Which was not published in English

This application claims priority of provisional application Serial No. Filed

19. CORRESPONDENCE ADDRESS

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Signature:	<i>Norman F. Oblon</i>	Date:	5/31/01
Name:		Registration No.:	

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

INVENTOR(S) Hiroyuki NAGASAWA, et al.

SERIAL NO: New Application

FILING DATE: Herewith

FOR: METHOD OF MANUFACTURING SILICON CARBIDE, SILICON CARBIDE, COMPOSITE MATERIAL, AND SEMICONDUCTOR ELEMENT

FEE TRANSMITTAL

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

FOR	NUMBER FILED	NUMBER EXTRA	RATE	CALCULATIONS
TOTAL CLAIMS	13 - 20 =	0	× \$18 =	\$0.00
INDEPENDENT CLAIMS	2 - 3 =	0	× \$80 =	\$0.00
■ MULTIPLE DEPENDENT CLAIMS (If applicable)			+ \$270 =	\$270.00
■ LATE FILING OF DECLARATION			+ \$130 =	\$130.00
			BASIC FEE	\$710.00
			TOTAL OF ABOVE CALCULATIONS	\$1,110.00
□ REDUCTION BY 50% FOR FILING BY SMALL ENTITY				\$0.00
□ FILING IN NON-ENGLISH LANGUAGE			+ \$130 =	\$0.00
□ RECORDATION OF ASSIGNMENT			+ \$40 =	\$0.00
			TOTAL	\$1,110.00

Please charge Deposit Account No. 15-0030 in the amount of A duplicate copy of this sheet is enclosed.

A check in the amount of **\$1,110.00** to cover the filing fee is enclosed.

The Commissioner is hereby authorized to charge any additional fees which may be required for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to Deposit Account No. 15-0030.
A duplicate copy of this sheet is enclosed.

Respectfully Submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.Date: 5/31/01

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Hiroyuki NAGASAWA, et al.

FILING DATE: Herewith

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LIST OF INVENTORS' NAMES AND ADDRESSES

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Listed below are the names and addresses of the inventors for the above-identified patent application.

Hiroyuki NAGASAWA	Tokyo, Japan
Takamitsu KAWAHARA	Kawasaki-shi, Japan
Kuniaki YAGI	Tokyo, Japan

A declaration containing all the necessary information will be submitted at a later date.

Respectfully Submitted,

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